

Yuuki Ishida

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

100
papers

1,365
citations

20
h-index

32
g-index

102
ext. papers

1,432
ext. citations

1.3
avg, IF

3.66
L-index

| # | Paper | IF | Citations |
|-----|---|-----|-----------|
| 100 | Quartz crystal microbalance for real-time monitoring chlorosilane gas transport in slim vertical cold wall chemical vapor deposition reactor. <i>Materials Science in Semiconductor Processing</i> , 2020 , 106, 104759-104764 | 4.3 | 1 |
| 99 | Advantages of a slim vertical gas channel at high SiHCl ₃ concentrations for atmospheric pressure silicon epitaxial growth. <i>Materials Science in Semiconductor Processing</i> , 2018 , 87, 13-18 | 4.3 | 4 |
| 98 | Real time evaluation of silicon epitaxial growth process by exhaust gas measurement using quartz crystal microbalance. <i>Materials Science in Semiconductor Processing</i> , 2018 , 88, 192-197 | 4.3 | 5 |
| 97 | Proposal of the mechanism for inclination growth on a mesa top during the 4H-SiC trench filling epitaxy. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 070307 | 1.4 | |
| 96 | Transport phenomena in a slim vertical atmospheric pressure chemical vapor deposition reactor utilizing natural convection. <i>Materials Science in Semiconductor Processing</i> , 2017 , 71, 348-351 | 4.3 | 5 |
| 95 | Repetition of In Situ Cleaning Using Chlorine Trifluoride Gas for Silicon Carbide Epitaxial Reactor. <i>ECS Journal of Solid State Science and Technology</i> , 2016 , 5, P12-P15 | 2 | 12 |
| 94 | Reflector Influence on Rapid Heating of Minimal Manufacturing Chemical Vapor Deposition Reactor. <i>ECS Journal of Solid State Science and Technology</i> , 2016 , 5, P280-P284 | 2 | 5 |
| 93 | Investigation of the giant step bunching induced by the etching of 4H-SiC in Ar/H ₂ mix gases. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 095501 | 1.4 | 4 |
| 92 | In Situ Cleaning Process of Silicon Carbide Epitaxial Reactor. <i>ECS Journal of Solid State Science and Technology</i> , 2015 , 4, P137-P140 | 2 | 14 |
| 91 | Epitaxial growth and characterization of thick multi-layer 4H-SiC for very high-voltage insulated gate bipolar transistors. <i>Journal of Applied Physics</i> , 2015 , 118, 085702 | 2.5 | 11 |
| 90 | Experiment on alleviating the bending of CVD-grown heavily Al-doped 4H-SiC epiwafer by codoping of N. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 04DP08 | 1.4 | 4 |
| 89 | Cleaning Process for Using Chlorine Trifluoride Gas Silicon Carbide Chemical Vapor Deposition Reactor. <i>Materials Science Forum</i> , 2015 , 821-823, 125-128 | 0.4 | 3 |
| 88 | Hopping conduction range of heavily Al-doped 4H-SiC thick epilayers grown by CVD. <i>Applied Physics Express</i> , 2015 , 8, 121302 | 2.4 | 8 |
| 87 | Investigation of giant step bunching in 4H-SiC homoepitaxial growth: Proposal of cluster effect model. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 061301 | 1.4 | 9 |
| 86 | Cleaning Process Applicable to Silicon Carbide Chemical Vapor Deposition Reactor. <i>ECS Journal of Solid State Science and Technology</i> , 2014 , 3, N3006-N3009 | 2 | 13 |
| 85 | Proposal of quasi thermal equilibrium model for etching phenomenon by gases: Example of the etching of 4H-SiC by H ₂ . <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 046501 | 1.4 | 6 |
| 84 | Epitaxial Growth of Thick Multi-Layer 4H-SiC for the Fabrication of Very High-Voltage C-Face n-Channel IGBT. <i>Materials Science Forum</i> , 2014 , 778-780, 135-138 | 0.4 | 8 |

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| 83 | Simulation Studies on Giant Step Bunching in 4H-SiC Epitaxial Growth: Cluster Effect. <i>Materials Science Forum</i> , 2014 , 778-780, 183-186 | 0.4 | 5 |
| 82 | Characterization of the Defect Evolution in Thick Heavily Al-Doped 4H-SiC Epilayers. <i>Materials Science Forum</i> , 2014 , 778-780, 151-154 | 0.4 | 3 |
| 81 | Simulation Studies on Giant Step Bunching Accompanying Trapezoid-Shape Defects in 4H-SiC Epitaxial Layer. <i>Materials Science Forum</i> , 2014 , 778-780, 222-225 | 0.4 | 5 |
| 80 | Suppressing Al memory effect on CVD growth of 4H-SiC epilayers by adding hydrogen chloride gas. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 04EP07 | 1.4 | 1 |
| 79 | The growth of low resistivity, heavily Al-doped 4H-SiC thick epilayers by hot-wall chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2013 , 380, 85-92 | 1.6 | 30 |
| 78 | Low Resistivity, Thick Heavily Al-Doped 4H-SiC Epilayers Grown by Hot-Wall Chemical Vapor Deposition. <i>Materials Science Forum</i> , 2013 , 740-742, 181-184 | 0.4 | 18 |
| 77 | Suppression of Al Memory-Effect on Growing 4H-SiC Epilayers by Hot-Wall Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 04CP04 | 1.4 | 1 |
| 76 | Two-Dimensional Roughness Growth at Surface and Interface of SiO ₂ Films during Thermal Oxidation of 4H-SiC(0001). <i>Materials Science Forum</i> , 2012 , 717-720, 785-788 | 0.4 | 4 |
| 75 | Recent Developments in the High-Rate Growth of SiC Epitaxial Layers by the Chemical Vapor Deposition Method. <i>Journal of the Vacuum Society of Japan</i> , 2011 , 54, 346-352 | | 3 |
| 74 | Experimental Verification of the Cluster Effect on Giant Step Bunching on 4H-SiC (0001) Surfaces. <i>Materials Science Forum</i> , 2010 , 645-648, 543-546 | 0.4 | 8 |
| 73 | RF-MBE growth of InN on 4H-SiC (0001) with off-angles. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010 , 7, 2016-2018 | | 2 |
| 72 | Shape Transformation of 4H-SiC Microtrenches by Hydrogen Annealing. <i>Japanese Journal of Applied Physics</i> , 2009 , 48, 041105 | 1.4 | 12 |
| 71 | Development of a Practical High-Rate CVD System. <i>Materials Science Forum</i> , 2008 , 600-603, 119-122 | 0.4 | 19 |
| 70 | Origin of Giant Step Bunching on 4H-SiC (0001) Surfaces. <i>Materials Science Forum</i> , 2008 , 600-603, 473-476 | 0.4 | 28 |
| 69 | Influence of Growth Conditions and Substrate Properties on Formation of Interfacial Dislocations and Dislocation Half-loop Arrays in 4H-SiC(0001) and (000-1) Epitaxy. <i>Materials Research Society Symposia Proceedings</i> , 2008 , 1069, 1 | | 9 |
| 68 | Reduction of defects propagating into 3C-SiC homoepilayers by reactive ion etching of 3C-SiC heteroepilayer substrates. <i>Journal of Crystal Growth</i> , 2007 , 308, 50-57 | 1.6 | 9 |
| 67 | Effect of Reduced Pressure on 3C-SiC Heteroepitaxial Growth on Si by CVD. <i>Chemical Vapor Deposition</i> , 2006 , 12, 495-501 | | 31 |
| 66 | Proposal of the Thermal Equilibrium Model for SiC Hydrogen Etching Phenomena. <i>Materials Science Forum</i> , 2006 , 527-529, 211-214 | 0.4 | 5 |

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| 65 | Dependence of stacking fault and twin densities on deposition conditions during 3C-SiC heteroepitaxial growth on on-axis Si(001) substrates. <i>Journal of Crystal Growth</i> , 2006 , 291, 140-147 | 1.6 | 19 |
| 64 | Reductions of twin and protrusion in 3C-SiC heteroepitaxial growth on Si(100). <i>Journal of Crystal Growth</i> , 2006 , 291, 148-153 | 1.6 | 18 |
| 63 | Effect of Ar post-oxidation annealing on oxide/4H-SiC interfaces studied by capacitance to voltage measurements and photoemission spectroscopy. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2005 , 23, 298-303 | 2.9 | 19 |
| 62 | In situ Observation of Clusters in Gas Phase during 4H-SiC Epitaxial Growth by Chemical Vapor Deposition Method. <i>Japanese Journal of Applied Physics</i> , 2004 , 43, 5140-5144 | 1.4 | 22 |
| 61 | 4H-SiC Carbon-Face Epitaxial Layers Grown by Low-Pressure Hot-Wall Chemical Vapor Deposition. <i>Materials Science Forum</i> , 2004 , 457-460, 209-212 | 0.4 | 2 |
| 60 | Relationship between the Current Direction in the Inversion Layer and the Electrical Characteristics of Metal-Oxide-Semiconductor Field Effect Transistors on 3C-SiC. <i>Materials Science Forum</i> , 2004 , 457-460, 1405-1408 | 0.4 | 2 |
| 59 | Photoemission Spectroscopic Studies on Oxide/SiC Interfaces Formed by Dry and Pyrogenic Oxidation. <i>Materials Science Forum</i> , 2004 , 457-460, 1341-1344 | 0.4 | 2 |
| 58 | Influence of C/Si Ratio on the 4H-SiC (0001) Epitaxial Growth and a Keynote for High-Rate Growth. <i>Materials Science Forum</i> , 2004 , 457-460, 213-216 | 0.4 | 12 |
| 57 | Recombination dynamics of localized excitons in cubic In _x Ga _{1-x} N/GaN multiple quantum wells grown by radio frequency molecular beam epitaxy on 3CβSiC substrate. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2003 , 21, 1856 | | 41 |
| 56 | The Electrical Characteristics of Metal-Oxide-Semiconductor Field Effect Transistors Fabricated on Cubic Silicon Carbide. <i>Japanese Journal of Applied Physics</i> , 2003 , 42, L625-L627 | 1.4 | 34 |
| 55 | Uniformity of 4HβSiC epitaxial layers grown on 3-in diameter substrates. <i>Journal of Crystal Growth</i> , 2003 , 258, 113-122 | 1.6 | 6 |
| 54 | Light emission versus energy gap in group-III nitrides: hydrostatic pressure studies. <i>Physica Status Solidi (B): Basic Research</i> , 2003 , 235, 225-231 | 1.3 | 11 |
| 53 | Anomalous pressure dependence of light emission in cubic InGa _N . <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003 , 2682-2685 | | |
| 52 | Influence of InN mole fraction on the recombination processes of localized excitons in strained cubic In _x Ga _{1-x} N/GaN multiple quantum wells. <i>Journal of Applied Physics</i> , 2003 , 93, 2051-2054 | 2.5 | 47 |
| 51 | N-channel MOSFETs fabricated on homoepitaxy-grown 3C-SiC films. <i>IEEE Electron Device Letters</i> , 2003 , 24, 466-468 | 4.4 | 32 |
| 50 | Investigation of antiphase domain annihilation mechanism in 3CβSiC on Si substrates. <i>Journal of Applied Physics</i> , 2003 , 94, 4676-4689 | 2.5 | 15 |
| 49 | Pressure Coefficients of the Light Emission in Cubic InGa _N Epilayers and Cubic InGa _N /Ga _N Quantum Wells. <i>Physica Status Solidi (B): Basic Research</i> , 2002 , 234, 759-763 | 1.3 | 4 |
| 48 | Different pressure coefficients of the light emission in cubic and hexagonal InGa _N /Ga _N quantum wells. <i>Applied Physics Letters</i> , 2002 , 81, 232-234 | 3.4 | 14 |

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|----|---|-----|----|
| 47 | Epitaxial Growth of (11-20) 4H-SiC Using Substrate Grown in the [11-20] Direction. <i>Materials Science Forum</i> , 2002 , 389-393, 195-198 | 0.4 | 5 |
| 46 | Measurements of the Depth Profile of the Refractive Indices in Oxide Films on SiC by Spectroscopic Ellipsometry. <i>Japanese Journal of Applied Physics</i> , 2002 , 41, 800-804 | 1.4 | 15 |
| 45 | Replication of Defects from 4H-SiC Wafer to Epitaxial Layer. <i>Materials Science Forum</i> , 2002 , 389-393, 447-450 | 0.4 | 4 |
| 44 | Influence of the Crystalline Quality of Epitaxial Layers on Inversion Channel Mobility in 4H-SiC MOSFETs. <i>Materials Science Forum</i> , 2002 , 389-393, 1053-1056 | 0.4 | 1 |
| 43 | 3C-SiC(100) Homoepitaxial Growth by Chemical Vapor Deposition and Schottky Barrier Junction Characteristics. <i>Materials Science Forum</i> , 2002 , 389-393, 275-278 | 0.4 | 4 |
| 42 | The Investigation of 4H-SiC/SiO ₂ Interfaces by Optical and Electrical Measurements. <i>Materials Science Forum</i> , 2002 , 389-393, 1013-1016 | 0.4 | 3 |
| 41 | Investigation of the Relationship between Defects and Electrical Properties of 3C-SiC Epilayers. <i>Materials Science Forum</i> , 2002 , 389-393, 459-462 | 0.4 | 2 |
| 40 | High-Rate Epitaxial Growth of 4H-SiC Using a Vertical-Type, Quasi-Hot-Wall CVD Reactor. <i>Materials Science Forum</i> , 2002 , 389-393, 179-182 | 0.4 | 14 |
| 39 | Investigation of Residual Impurities in 4H-SiC Epitaxial Layers Grown by Hot-Wall Chemical Vapor Deposition. <i>Materials Science Forum</i> , 2002 , 389-393, 215-218 | 0.4 | 6 |
| 38 | Simulation of High-Temperature SiC Epitaxial Growth Using Vertical, Quasi-Hot-Wall CVD Reactor. <i>Materials Science Forum</i> , 2002 , 389-393, 227-230 | 0.4 | 6 |
| 37 | Sensitive Detection of Defects in 4H-SiC by Raman Scattering. <i>Materials Science Forum</i> , 2002 , 389-393, 629-632 | 0.4 | 6 |
| 36 | Characterization of the Interfaces between SiC and Oxide Films by Spectroscopic Ellipsometry. <i>Materials Science Forum</i> , 2002 , 389-393, 1029-1032 | 0.4 | 3 |
| 35 | Influence of stacking faults on the performance of 4H-SiC Schottky barrier diodes fabricated on (112 0) face. <i>Applied Physics Letters</i> , 2002 , 81, 2974-2976 | 3.4 | 22 |
| 34 | Comparative Study of Heteroepitaxially and Homoepitaxially Grown 3C-SiC Films. <i>Materials Science Forum</i> , 2002 , 389-393, 323-326 | 0.4 | 6 |
| 33 | Detection of defects in SiC crystalline films by Raman scattering. <i>Physica B: Condensed Matter</i> , 2001 , 308-310, 684-686 | 2.8 | 51 |
| 32 | Electrical Characterization at Cubic AlN/GaN Heterointerface Grown by Radio-Frequency Plasma-Assisted Molecular Beam Epitaxy. <i>Physica Status Solidi (B): Basic Research</i> , 2001 , 228, 599-602 | 1.3 | 3 |
| 31 | Optical Properties of Cubic InGaN/GaN Multiple Quantum Wells on 3C-SiC Substrates by Radio-Frequency Plasma-Assisted Molecular Beam Epitaxy. <i>Physica Status Solidi A</i> , 2001 , 188, 705-709 | | 9 |
| 30 | Growth and characterization of cubic InGaN epilayers on 3C-SiC by RF MBE. <i>Journal of Crystal Growth</i> , 2001 , 227-228, 471-475 | 1.6 | 20 |

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|----|---|-----|----|
| 29 | Control of Surface Morphologies for Epitaxial Growth on Low Off-Angle 4H-SiC (0001) Substrates. <i>Materials Science Forum</i> , 2001 , 353-356, 135-138 | 0.4 | 4 |
| 28 | Optical and structural studies in InGaN quantum well structure laser diodes. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2001 , 19, 2177 | | 66 |
| 27 | Localized exciton dynamics in strained cubic In _{0.1} Ga _{0.9} N/GaN multiple quantum wells. <i>Applied Physics Letters</i> , 2001 , 79, 4319-4321 | 3.4 | 72 |
| 26 | Band gap bowing and exciton localization in strained cubic In _x Ga _{1-x} N films grown on 3C-SiC (001) by rf molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2001 , 79, 3600-3602 | 3.4 | 17 |
| 25 | Similarities in the Optical Properties of Hexagonal and Cubic InGaN Quantum Wells. <i>Materials Research Society Symposia Proceedings</i> , 2001 , 693, 722 | | |
| 24 | Piezoelectric Field and its Influence on the Pressure Behavior of the Light Emission from InGaN/GaN and GaN/AlGaIn Quantum Wells. <i>Materials Research Society Symposia Proceedings</i> , 2001 , 693, 728 | | |
| 23 | Optical Constants of Cubic GaN, AlN, and AlGaIn Alloys. <i>Japanese Journal of Applied Physics</i> , 2000 , 39, L497-L499 | 1.4 | 44 |
| 22 | Characterization of Oxide Films on SiC by Spectroscopic Ellipsometry. <i>Japanese Journal of Applied Physics</i> , 2000 , 39, L1054-L1056 | 1.4 | 17 |
| 21 | Effects of Steam Annealing on Electrical Characteristics of 3C-SiC Metal-Oxide-Semiconductor Structures. <i>Materials Science Forum</i> , 2000 , 338-342, 1129-1132 | 0.4 | |
| 20 | Observation of Cubic GaN/AlN Heterointerface Formation by RHEED in Plasma-Assisted Molecular Beam Epitaxy. <i>Materials Science Forum</i> , 2000 , 338-342, 1545-1548 | 0.4 | 1 |
| 19 | The APD Annihilation Mechanism of 3C-SiC Hetero-Epilayer on Si(001) Substrate. <i>Materials Science Forum</i> , 2000 , 338-342, 253-256 | 0.4 | 5 |
| 18 | Schottky Barrier Characteristics of 3C-SiC Epilayers Grown by Low Pressure Chemical Vapor Deposition. <i>Materials Science Forum</i> , 2000 , 338-342, 1235-1238 | 0.4 | 4 |
| 17 | Pre-Growth Treatment of 4H-SiC Substrates by Hydrogen Etching at Low Pressure. <i>Materials Science Forum</i> , 2000 , 338-342, 1037-1040 | 0.4 | 9 |
| 16 | Coimplantation Effects of (C and Si)/Ga in 6H-SiC. <i>Materials Science Forum</i> , 2000 , 338-342, 917-920 | 0.4 | 2 |
| 15 | Competitive Growth between Deposition and Etching in 4H-SiC CVD Epitaxy Using Quasi-Hot Wall Reactor. <i>Materials Science Forum</i> , 2000 , 338-342, 169-172 | 0.4 | 9 |
| 14 | Elongated shaped Si Island Formation on 3C-SiC by Chemical Vapor Deposition and Its Application to Antiphase Domain Observation. <i>Japanese Journal of Applied Physics</i> , 1999 , 38, 3470-3474 | 1.4 | 14 |
| 13 | Growth and characterization of cubic AlGaIn and AlN epilayers by RF-plasma assisted MBE. <i>Journal of Crystal Growth</i> , 1999 , 201-202, 341-345 | 1.6 | 24 |
| 12 | Optical Characterization of Cubic AlGaIn Epilayers by Cathodoluminescence and Spectroscopic Ellipsometry. <i>Physica Status Solidi (B): Basic Research</i> , 1999 , 216, 211-214 | 1.3 | 9 |

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|----|--|-----|----|
| 11 | Raman studies on phonon modes in cubic AlGa _N alloy. <i>Applied Physics Letters</i> , 1999 , 74, 191-193 | 3.4 | 67 |
| 10 | Growth of cubic III-nitrides by gas source MBE using atomic nitrogen plasma: GaN, AlGa _N and AlN. <i>Journal of Crystal Growth</i> , 1998 , 189-190, 390-394 | 1.6 | 65 |
| 9 | Raman scattering characterization of group III-nitride epitaxial layers including cubic phase. <i>Journal of Crystal Growth</i> , 1998 , 189-190, 435-438 | 1.6 | 14 |
| 8 | Arsenic surfactant effects and arsenic mediated molecular beam epitaxial growth for cubic GaN. <i>Applied Physics Letters</i> , 1998 , 72, 3056-3058 | 3.4 | 57 |
| 7 | CVD Growth Mechanism of 3C-SiC on Si Substrates. <i>Materials Science Forum</i> , 1998 , 264-268, 183-186 | 0.4 | 4 |
| 6 | The Characterization of SiC Hot-Implanted with Ga +. <i>Materials Science Forum</i> , 1998 , 264-268, 713-716 | 0.4 | 2 |
| 5 | Surface Reconstruction and As Surfactant Effects on MBE-Grown GaN Epilayers. <i>Materials Science Forum</i> , 1998 , 264-268, 1167-1172 | 0.4 | 7 |
| 4 | Investigation of Positron Moderator Materials for Electron-Linac-Based Slow Positron Beamlines. <i>Japanese Journal of Applied Physics</i> , 1998 , 37, 4636-4643 | 1.4 | 22 |
| 3 | Surface Morphology of 3C-SiC Heteroepitaxial Layers Grown by LPCVD on Si Substrates. <i>Materials Science Forum</i> , 1998 , 264-268, 207-210 | 0.4 | 6 |
| 2 | Atomically Flat 3C-SiC Epilayers by Low Pressure Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , 1997 , 36, 6633-6637 | 1.4 | 34 |
| 1 | Positron Lifetime Study on Semiconductor Thin Films. <i>Materials Science Forum</i> , 1997 , 255-257, 714-717 | 0.4 | 5 |